

<b>Form 1449 (Modified)</b>  <b>Information Disclosure Statement By Applicant</b>  (Use Several Sheets if Necessary)	Atty Docket No.	Application No.:
	<b>LAM1P185/P1228</b>	<b>Filed Herewith</b>
	Applicant:	
	<b>RAMALINGAM et al.</b>	
	Filing Date	Group
	<b>Herewith</b>	<b>Unassigned</b>

#### U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
JO	A	3,398,033	08/20/68	Haga et al.	156	17	02/26/65
	B	4,351,894	09/28/82	Yonezawa et al.	430	313	05/12/81
	C	4,595,453	06/17/86	Yamazaki et al.	156	643	09/24/84
	D	4,865,685	09/12/89	Palmour	156	643	11/03/87
	E	4,981,551	01/01/91	Palmour	156	643	09/06/89
	F	6,090,304	07/18/00	Zhu et al.	216	79	08/28/97
	G	6,432,779B1	08/13/02	Hobbs et al.	438	287	01/30/01
	H	6,451,647B1	09/17/02	Yang et al.	438	240	03/18/02
	I	6,511,872B1	01/28/03	Donnelly, Jr. et al.	438	197	07/10/01
	J	20030000546	01/02/03	Richardson et al.	134	1.1	05/03/02
JO	K	20030170986	09/11/03	Nallan et al.	438	689	03/06/02

#### Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No
	L							
	M							
	N							

#### Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
JO	O	Pelhos et al., "Etching of High-K Dielectric $Zr_{1-x}Al_xO_y$ Films in Chlorine-Containing Plasmas", J. Vac. Sci. Technol. A 19(4), Jul/Aug 2001, pages 1361-1366
JO	P	Sha et al., "Plasma Etching Selectivity of $ZrO_2$ to Si in $BCl_3/Cl_2$ Plasmas", J. Vac. Sci. Technol. A 21(6), Nov/Dec 2003, pages 1915-1922
	Q	
Examiner	JO	Date Considered 8/30/05

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.